

**SEMITOP<sup>®</sup> 2**

## IGBT Module

### SK 14 GD 063

#### Target Data

#### Features

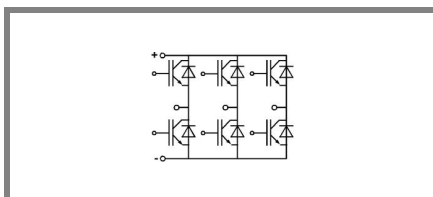
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence

#### Typical Applications

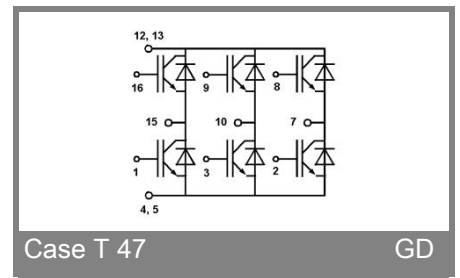
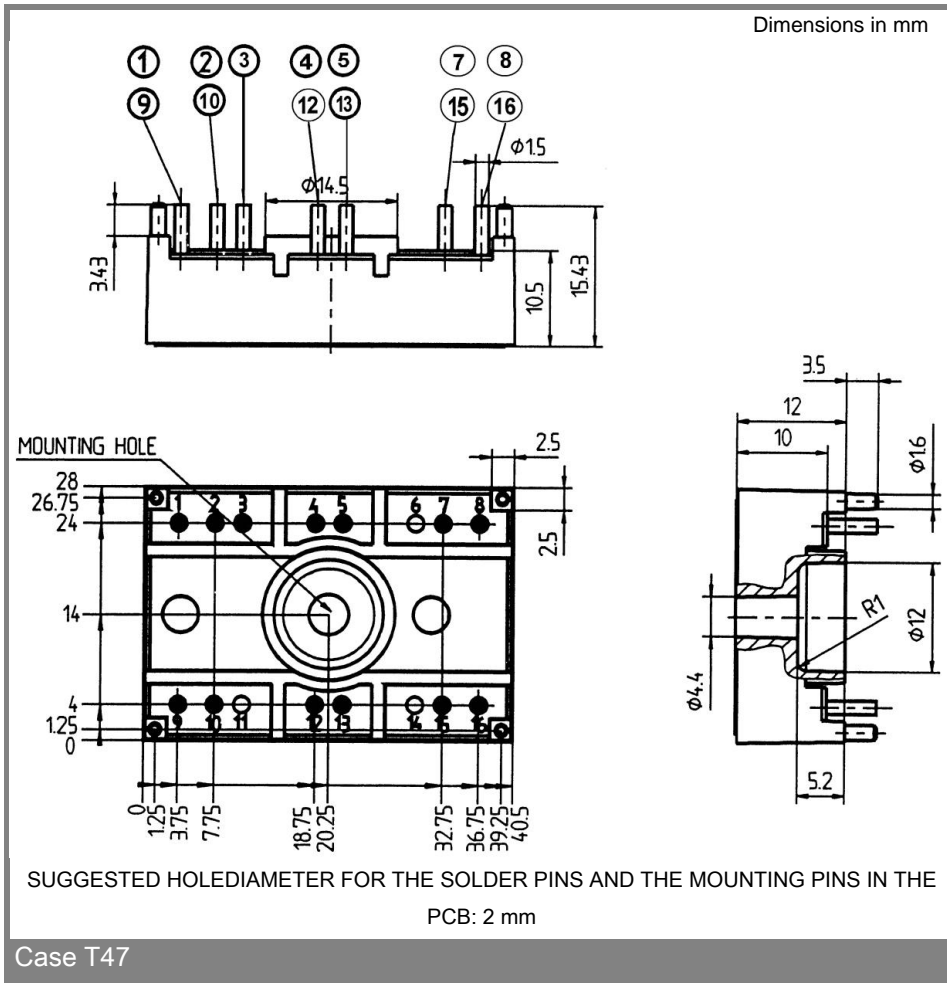
- Switching ( not for linear use )
- Inverter
- Switched mode power supplies
- UPS

Absolute Maximum Ratings		$T_s = 25\text{ }^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$		600	V
$V_{GES}$		$\pm 20$	V
$I_C$	$T_s = 25\text{ (80) }^\circ\text{C}$ ;	18 (13)	A
$I_{CM}$	$t_p < 1\text{ ms}$ ; $T_s = 25\text{ (80) }^\circ\text{C}$ ;	36 (26)	A
$T_j$		- 40 ... + 150	$^\circ\text{C}$
<b>Inverse / Freewheeling CAL diode</b>			
$I_F = -I_C$	$T_s = 25\text{ (80) }^\circ\text{C}$ ;	22 (15)	A
$I_{FM} = -I_{CM}$	$t_p < 1\text{ ms}$ ; $T_s = 25\text{ (80) }^\circ\text{C}$ ;	44 (30)	A
$T_j$		- 40 ... + 150	$^\circ\text{C}$
$T_{stg}$		- 40 ... + 125	$^\circ\text{C}$
$T_{sol}$	Terminals, 10 s	260	$^\circ\text{C}$
$V_{isol}$	AC 50 Hz, r.m.s. 1 min. / 1 s	2500 / 3000	V

Characteristics		$T_s = 25\text{ }^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 10\text{ A}$ , $T_j = 25\text{ (125) }^\circ\text{C}$		2,1 (2,4)	2,5 (2,8)	V
$V_{GE(th)}$	$V_{CE} = V_{GE}$ ; $I_C = 0,0004\text{ A}$	4,5	5,5	6,5	V
$C_{res}$	$V_{CE} = 25\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; 1 MHz		0,57		nF
$R_{th(j-s)}$	per IGBT per module			2	K/W K/W
$t_{d(on)}$	under following conditions: $V_{CC} = 300\text{ V}$ , $V_{GE} = \pm 15\text{ V}$		45		ns
$t_r$	$I_C = 10\text{ A}$ , $T_j = 125\text{ }^\circ\text{C}$		45		ns
$t_{d(off)}$	$R_{Gon} = R_{Goff} = 100\text{ }\Omega$		250		ns
$t_f$			20		ns
$E_{on} + E_{off}$	Inductive load		1		mJ
<b>Inverse / Freewheeling CAL diode</b>					
$V_F = V_{EC}$	$I_F = 10\text{ A}$ ; $T_j = 25\text{ (125) }^\circ\text{C}$		1,45 (1,4)	1,7 (1,7)	V
$V_{(TO)}$	$T_j = (125)\text{ }^\circ\text{C}$		(0,85)	(0,9)	V
$r_T$	$T_j = (125)\text{ }^\circ\text{C}$		(55)	(80)	m $\Omega$
$R_{th(j-s)}$				2,3	K/W
$I_{RRM}$	under following conditions: $I_F = 10\text{ A}$ ; $V_R = -300\text{ V}$		6,5		A
$Q_{rr}$	$di_F/dt = -200\text{ A}/\mu\text{s}$		1		$\mu\text{C}$
$E_{off}$	$V_{GE} = 0\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$		0,1		mJ
<b>Mechanical data</b>					
M1	mounting torque			2	Nm
w			21		g
Case	SEMITOP <sup>®</sup> 2		T 47		



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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